鼎德丰
DING DE FENG

NPN Silicon Transistor

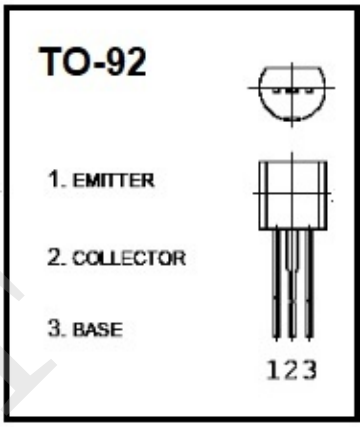
2SC3279

Features

- **Package:TO-92**

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector-base voltage	BV_{CBO}	30	V
Collector-emitter voltage	BV_{CEO}	10	V
Emitter-base voltage	BV_{EBO}	6	V
Collector current	I_{CM}	2	A
Collector Power Dissipation	P_C	750	mW
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55～+150	℃



Electrical Characteristics（Ta=25℃）

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=1mA，I_E=0	30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=10mA，I_B=0	10			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=1mA，I_C=0	6			V
collector-base cut-off current	I_{CBO}	V_{CB}=30V，I_E=0			0.1	μA
emitter-base cut-off current	I_{EBO}	V_{EB}=6V，I_C=0			0.1	μA
DC current gain	H_{FE}	V_{CE}=1V，I_C=500mA	140		600	
collector-emitter saturation voltage	V_{CESAT}	I_C=2A，I_B=100mA			0.82	V
Base-Emitter Saturation Voltage	V_{BESAT}	I_C=2A，I_B=100mA			1.2	
Transition frequency	f_T	V_{CE}=1V，I_C=500mA	150	150		MHz

Classification of H_{FE}

Rank	O	Y
Range	70-140	120-240